

ABSTRACT

There are provided a semiconductor memory device and a manufacturing method thereof. The semiconductor memory device may include a gate stack structure having a stepped structure, which includes
5 a plurality of interlayer insulating layers and a plurality of conductive layers, a tubular insulating layer penetrating the stepped structure of the gate stack structure, and a conductive gate contact connected to an end portion of one of the plurality of conductive layers, the conductive gate contact extending to a central region of the tubular insulating layer.

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FIG. 10C